

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	462418	plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 10:47
S2	199877	etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 10:47
S3	17184	S1 near S2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 10:48
S4	60405	Chang.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 10:49
S5	374	S3 and S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 10:48
S8	29319	Chang adj et	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 10:49
S9	1293	S4 and S8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 10:49
S10	22	S3 and S9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 10:50
S11	1026571	silicon nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 10:50

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S12	21	S10 and S11	US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB	ON	2005/08/29 11:04	
S13	2	"5,665,203".pn.	US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB	ON	2005/08/29 15:57	
S14	1437754	LTO near silicon oxide	US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB	ON	2005/08/29 13:21	
S15	41	LTO near (silicon adj oxide)	US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB	ON	2005/08/29 14:04	
S16	1759114	treatment	US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB	ON	2005/08/29 14:04	
S17	462418	plasma	US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB	ON	2005/08/29 14:04	
S18	172453	S17 and S16	US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB	ON	2005/08/29 14:05	
S19	24255	S17 near S16	US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB	ON	2005/08/29 14:05	
S20	25	("5665203").URPN.	USPAT	OR	ON	2005/08/29 14:16
S21	8815	S16 near S17	USPAT	OR	ON	2005/08/29 14:16
S22	8815	S17 near S16	USPAT	OR	ON	2005/08/29 14:17
S23	282047	bias	USPAT	OR	ON	2005/08/29 14:20
S24	289707	S22 nead S23	USPAT	OR	ON	2005/08/29 14:17
S25	2991911	zero or no	USPAT	OR	ON	2005/08/29 14:17
S26	2	S22 near S23	USPAT	OR	ON	2005/08/29 15:33

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S27	125166	RF	USPAT	OR	ON	2005/08/29 14:20
S28	62	S22 near S27	USPAT	OR	ON	2005/08/29 14:22
S29	8432	plasma near etch	USPAT	OR	ON	2005/08/29 14:22
S30	3	S28 and S29	USPAT	OR	ON	2005/08/29 14:23
S31	3669	reduce near (charge or charging)	USPAT	OR	ON	2005/08/29 14:23
S32	571	S31 and S17	USPAT	OR	ON	2005/08/29 14:23
S33	222	S32 and S23	USPAT	OR	ON	2005/08/29 14:24
S34	106	S33 and S27	USPAT	OR	ON	2005/08/29 14:24
S35	547792	inert or ambient	USPAT	OR	ON	2005/08/29 14:24
S36	58	S34 and S35	USPAT	OR	ON	2005/08/29 14:29
S37	12	S36 and S29	USPAT	OR	ON	2005/08/29 14:29
S38	20853	PMOS	USPAT	OR	ON	2005/08/29 15:33
S39	0	"6656832.pn"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 15:58
S40	2	"6656832".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 15:59
S41	436442	high adj frequency	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:00
S42	211441	MHz	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:00
S43	689	S41 near S41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:00
S44	11	zero near (RF adj bias)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:15

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S45	0	S44 and S43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:00
S46	1	09/775664	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:08
S47	8	inductively adj coupled near plasma near etch.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:16
S48	0	inductively adj coupled near etch. ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:17
S49	866	inductively adj coupled and etch.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:17
S50	328	S49 and RIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:17
S51	208	S50 and bias	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:17
S52	172	S51 and RF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:17
S53	107	S52 and MHZ	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:29
S54	2305	(no or zero) near bis	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:29

EAST Search History

S55	0	S53 and S54	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:30
S56	2641	overetch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:30
S57	3993	no near bias	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:30
S58	35	S56 and S57	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:40
S59	2127396	substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 07:32
S60	1621	(gate adj dielectric) near (((silicon adj dioxide) or (SiO2 or SiOx or SiOn or "SiO.sub2" or "SiO.subx" or "SiO.subn" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.n")) or (high near (constant or k)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 07:34
S62	21352	polysilicon near gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 07:51
S63	981	(hard adj mask) near (((silicon adj dioxide) or (SiO2 or SiOx or SiOn or "SiO.sub2" or "SiO.subx" or "SiO.subn" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.n")) or ((silicon adj nitride) or (SiN4 or SiNn or "SiN.sub4" or "SiN.subx" or "SiN.subn" or "SiN.sub.4" or "SiN.sub.x" or "SiN.sub.n")) or ((SiO3N4 or "Si.O. sub.3N.sub.4" or "Si.O.sub.xN.sub.x" or "Si.O.sub.nN.sub.n" or "Si.O.sub.xN.sub.n" or "Si.O.sub.nN.sub.x")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 07:51

EAST Search History

S64	655	S59 and S60 and S62	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 07:39
S66	1	10/634001	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 08:18
S67	12	S64 and S63	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 07:44
S68	13773	(hard adj mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 07:51
S69	101	S60 and S62 and S68	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 07:51
S70	712	(polysilicon near gate).ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 07:57
S71	2	S69 and S70	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 07:52
S74	3569	polysilicon near etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 08:18
S76	135	bulk adj etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 08:19
S77	4390	over adj etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 08:19

EAST Search History

S78	10	S74 and S76 and S77	US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB	ON	2006/03/08 08:24
S79	0	S78 and bias	US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB	ON	2006/03/08 08:24
S80	876	S74 and bias	US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB	ON	2006/03/08 08:24
S81	793	S80 and source	US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB	ON	2006/03/08 08:25
S82	0	S81 and S76	US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB	ON	2006/03/08 15:17
S83	32	S81 and ((polysilicon near etch).ab.)	US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB	ON	2006/03/08 08:35
S84	52215	lower near power	US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB	ON	2006/03/08 08:35
S85	2188	expose near gate	US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB	ON	2006/03/08 08:40
S86	66	S84 and S85	US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB	ON	2006/03/08 08:35
S87	74	expose near gate near dielectric	US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB	ON	2006/03/08 08:40

EAST Search History

S88	4	S84 and S87	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 08:41
S89	1	"3" near step near polysilicon near etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 08:42
S90	2	"4" near step near polysilicon near etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 08:52
S91	2	"5242536".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 09:05
S92	7	AMAT and Cl2 and HBr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 09:05
S93	6	AMAT and Cl2 and HBr and polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 09:07
S94	6	AMAT and Cl2 and HBr and (polysilicon adj etch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 09:07
S95	28	AMAT and (polysilicon adj etch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 09:29
S98	1	plasma near treat near gate near dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 09:33
S99	2	"5273920".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 09:44

EAST Search History

S10 0	3	"6902681".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 10:31
S10 1	2	"6479403".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 10:32
S10 2	2	"6579809".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 12:26
S10 3	0	polysilicon near overetch near zero near bias	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 13:11
S10 4	0	polysilicon and (overetch near zero near bias)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 13:11
S10 5	17	polysilicon and overetch and (zero near bias)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 13:16
S10 6	1	polysilicon and overetch and (zero near rf)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 13:17
S10 7	1	overetch and (zero near rf)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 13:17
S10 8	7	(zero near rf near bias)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 15:16
S10 9	6708	(source and bias) near power	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 15:17

EAST Search History

S11 0	3569	polysilicon near etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 15:17
S11 1	177	S109 and S110	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 15:17
S11 2	4	S111 and HBr and Cl2 and O2 and CF4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 15:22
S11 3	2	09/875069	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 15:23
S11 4	2	S112 and S113	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 15:23